



30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	5.0mΩ @ V _{GS} = 10V	60A
30V	7.4mΩ @ V _{GS} = 4.5V	50A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

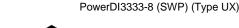
- Low R_{DS(ON)} ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN3009LFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

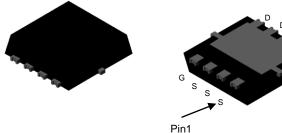
https://www.diodes.com/quality/product-definitions/

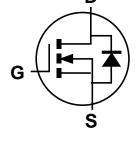
Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.

 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)







Equivalent Circuit

Ordering Information (Note 4)

Top View

Part Number	Case	Packaging
DMN3009LFVWQ-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMN3009LFVWQ-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

Bottom View

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



SW1 = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 19 = 2019)

WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	30	V	
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = 10V	$T_C = +25$ °C $T_C = +70$ °C	ΔD	60 48	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	90	Α	
Maximum Continuous Body Diode Forward Current (Note 7)	Is	60	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	90	Α
Avalanche Current, L = 0.1mH (Note 8)	I _{AS}	33	Α	
Avalanche Energy, L = 0.1mH (Note 8)	E _{AS}	58	mJ	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	126	°C/W
Total Power Dissipation (Note 6)		P_{D}	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	62	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	4.6	C/VV
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C

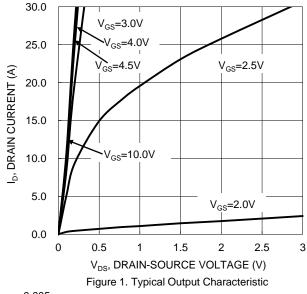
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	1	٧	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	3.5	5.0	mΩ	$V_{GS} = 10V, I_D = 30A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	_	4.9	7.4		$V_{GS} = 4.5V, I_D = 15A$	
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	2,000	_	pF		
Output Capacitance	Coss	_	315	1	рF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	247		pF	T = TIVIHZ	
Gate Resistance	R_g	_	2.2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	20	_	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	_	42	_	nC	\/ 45\/ L 45A	
Gate-Source Charge	Q _{gs}	_	4.7	_	nC	$V_{DS} = 15V, I_{D} = 15A$	
Gate-Drain Charge	Q_{gd}	_	7.4	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	3.9	_	ns		
Turn-On Rise Time	t _R	_	4.1	-	ns	$V_{DD} = 15V, V_{GS} = 10V,$ $R_G = 3.3\Omega, I_D = 15A$	
Turn-Off Delay Time	t _{D(OFF)}	_	31	_	ns		
Turn-Off Fall Time	t _F	_	15	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	15	_	ns	1 15 A di/dt 100 A/v.c	
Body Diode Reverse Recovery Charge	Q_{RR}	_	6.0	_	nC	$I_F = 15A$, di/dt = 100A/ μ s	

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_{J} = +25°C.
- Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





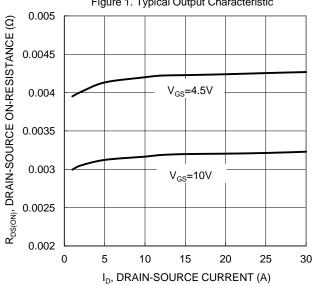


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

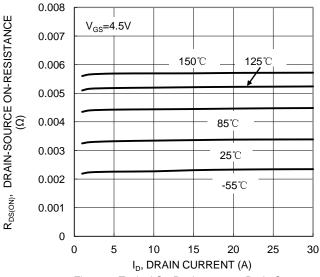


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

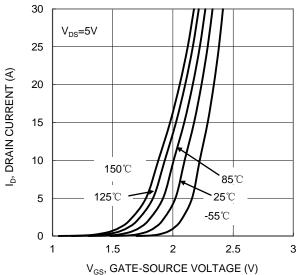


Figure 2. Typical Transfer Characteristic 0.02 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE (Ω) 0.016 0.012 0.008 $I_D=15A$ 0.004 0 8 12 0 4 16 20 V_{GS}, GATE-SOURCE VOLTAGE (V)

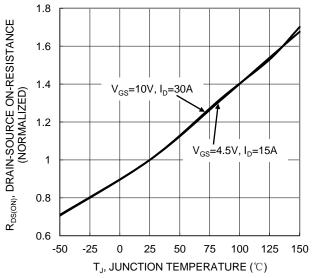


Figure 4. Typical Transfer Characteristic

Figure 6. On-Resistance Variation with Temperature



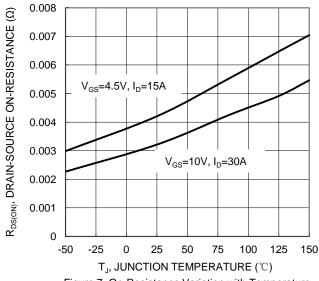


Figure 7. On-Resistance Variation with Temperature

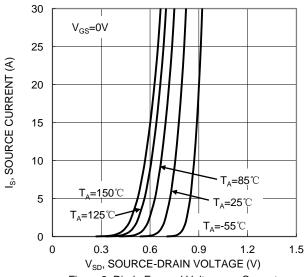


Figure 9. Diode Forward Voltage vs. Current

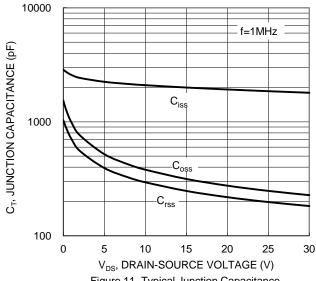


Figure 11. Typical Junction Capacitance

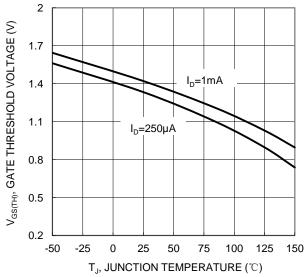


Figure 8. Gate Threshold Variation vs. Junction Temperature

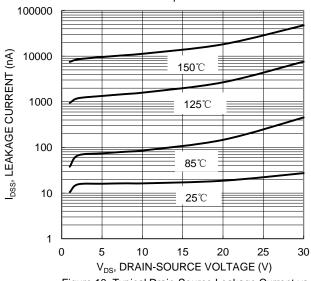


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

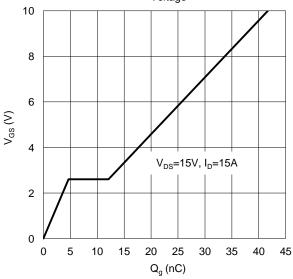
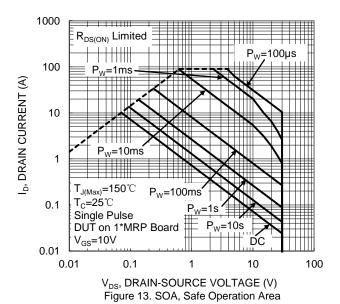


Figure 12. Gate Charge





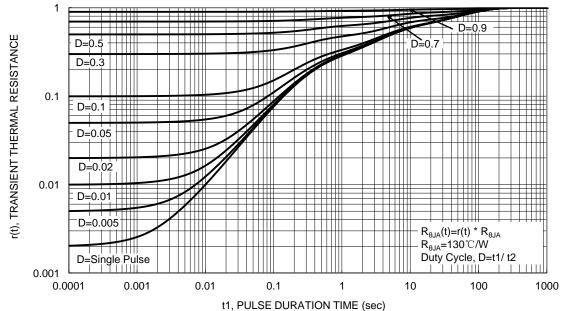


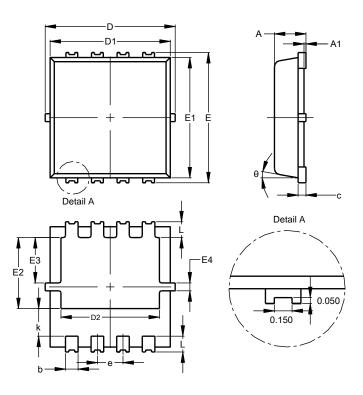
Figure 14. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

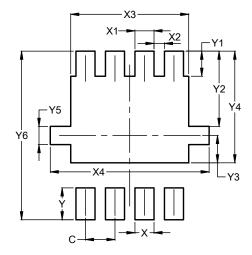


PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min	Тур				
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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